

ZXMP4A16K 40V P-channel enhancement mode MOSFET

Summary

 $V_{(BR)DSS}$ = -40V; $R_{DS(ON)}$ = 0.060 Ω I_{D} = -9.9A

Description

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



Features

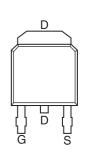
- · Low on-resistance
- · Fast switching speed
- · Low threshold
- · Low gate drive
- DPAK package

Applications

- DC DC converters
- · Audio output stages
- · Relay and solenoid driving
- · Motor control

Ordering information

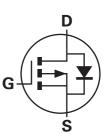
Device	Reel size (inches)	Tape width	Quantity per reel		
ZXMP4A16KTC	13	16mm	2500 units		



Pinout - Top view

Device marking

ZXMP 4A16



Absolute maximum rating

Parameter	Symbol	Limit	Unit					
Drain-source voltage	V _{DSS}	-40	V					
Gate-source voltage	V _{GS}	±20	V					
Continuous drain current								
V _{GS} = -10V; T _A =25°C ^(b)		-9.9	Α					
V _{GS} = -10V; T _A =70°C ^(b)	I _D	-8.0	Α					
V_{GS} = -10V; T_A =25°C ^(a)		-6.6	Α					
Pulsed drain current (c)	I _{DM}	-35	Α					
Continuous source current (body diode) (b)	I _S	-10.1	Α					
Pulsed source current (body diode) (c)	I _{SM}	-35	Α					
Power dissipation at T _A =25°C ^(a)	P _D	4.2	W					
Linear derating factor		33.6	mW/°C					
Power dissipation at T _A =25°C ^(b)	P _D	9.5	W					
Linear derating factor		76	mW/°C					
Power dissipation at T _A =25°C ^(d) Linear derating factor	P _D 2.15 17.2		W mW/°C					
Operating and storage temperature range	T _j :T _{stg}	-55 to +150	°C					
Thermal resistance								
Parameter	Symbol	Value	Unit					
Junction to ambient ^(a)	$R_{\Theta JA}$	30	°C/W					
Junction to ambient ^(b)	$R_{\Theta JA}$	13.2	°C/W					
Junction to ambient ^(d)	$R_{\Theta JA}$	58	°C/W					

NOTES:

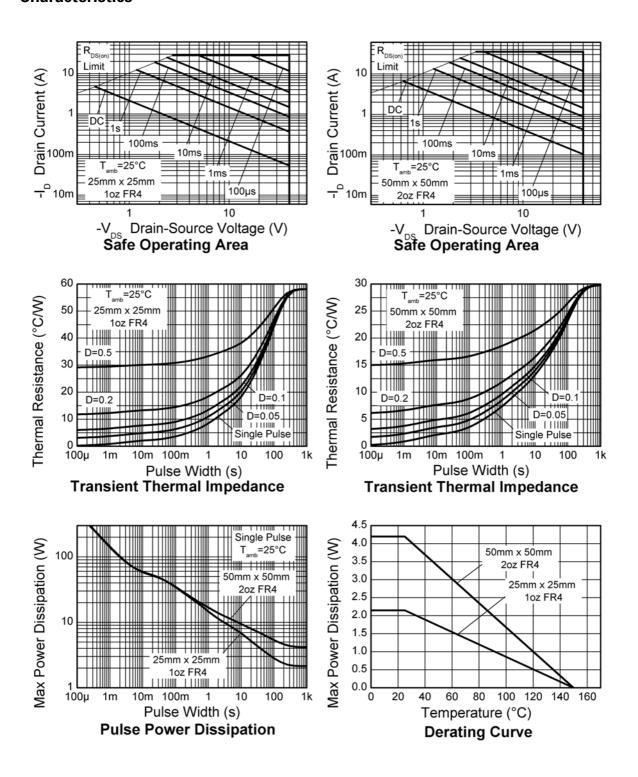
⁽a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

⁽b) For a device surface mounted on FR4 PCB measured at t $\leq\!10$ sec.

⁽c) Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, D=0.02 pulse width=300 \(\mu s \) - pulse width limited by maximum junction temperature.

⁽d) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

Characteristics



Electrical characteristics (at $T_A = 25$ °C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Static							
Drain-source breakdown voltage	V _{(BR)DSS}	-40			V	I _D =-250μA, V _{GS} =0V	
Zero gate voltage drain current	I _{DSS}			-1	μΑ	V _{DS} =-40V, V _{GS} =0V	
Gate-body leakage	I_{GSS}			100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
Gate-source threshold voltage	V _{GS(th)}	-1.0			V	I_D =-250 μ A, V_{DS} = V_{GS}	
Static drain-source on-state	R _{DS(on)}			0.060	Ω	V _{GS} =-10V, I _D =-3.8A	
resistance (*)				0.100	Ω	V_{GS} =-4.5V, I_{D} =-2.9A	
Forward transconductance (*)(‡)	9 _{fs}		7.4		S	V _{DS} =-15V,I _D =-3.8A	
Dynamic (‡)			•			•	
Input capacitance	C _{iss}		965		pF		
Output capacitance	C _{oss}		180		pF	V _{DS} =-20V, V _{GS} =0V, f=1MHz	
Reverse transfer capacitance	C _{rss}		158		pF	- I = I IVI T	
Switching (†) (‡)			•			•	
Turn-on delay time	t _{d(on)}		4.0		ns		
Rise time	t _r		6.0		ns	V _{DD} =-20V, I _D =-1A	
Turn-off delay time	t _{d(off)}		36.8		ns	$R_G=6.0\Omega$, $V_{GS}=-10V$	
Fall time	t _f		17.1		ns		
Gate charge	Q_g		16.5		nC	V_{DS} =-20V, V_{GS} =-5V, I_{D} =-3.8A	
Total gate charge	Qg		29.6		nC		
Gate-source charge	Q _{gs}		2.8		nC	V_{DS} =-20V, V_{GS} =-10V, I_{D} =-3.8A	
Gate-drain charge	Q_{gd}		8.1		nC	-1D- 0.0A	
Source-drain diode							
Diode forward voltage (*)	V _{SD}		-0.89	-1.2	V	T _J =25°C, I _S =-3.8A, V _{GS} =0V	
Reverse recovery time (‡)	t _{rr}		29.8		ns	T _J =25°C, I _F =-3.8A,	
Reverse recovery charge (‡)	O _{rr}		37.2		nC	di/dt= 100A/μs	

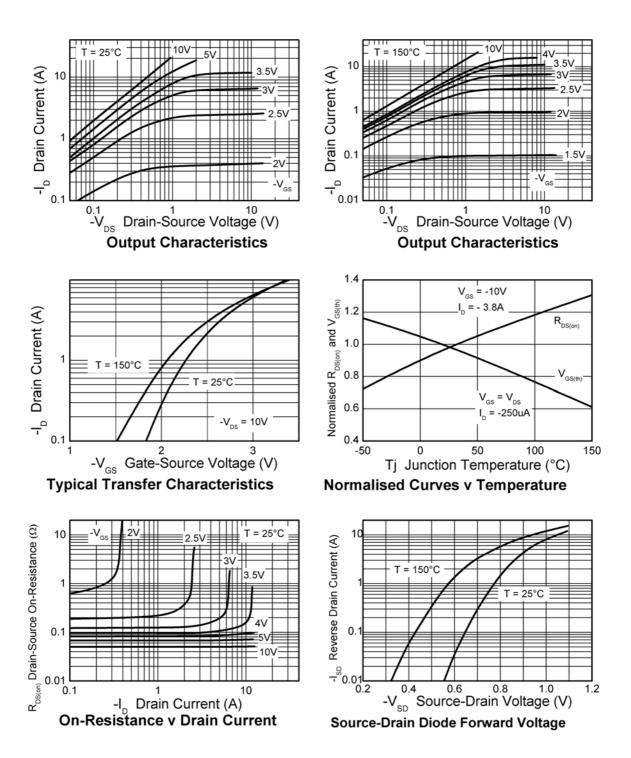
NOTES:

^(*) Measured under pulsed conditions. Width \leq 300µs. Duty cycle \leq 2%.

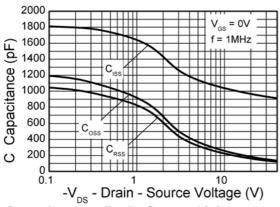
^(†) Switching characteristics are independent of operating junction temperature.

^(‡) For design aid only, not subject to production testing.

Typical characteristics



Typical characteristics

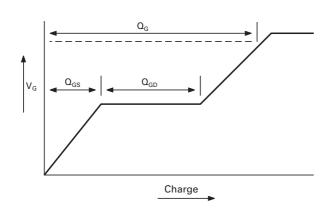


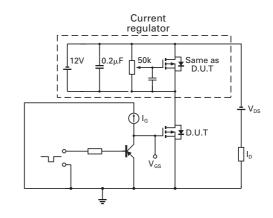
Source Voltage (nC)

| Source | Source

Capacitance v Drain-Source Voltage

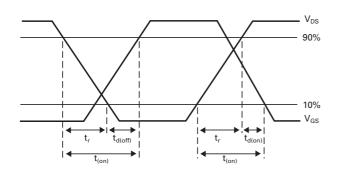
Gate-Source Voltage v Gate Charge

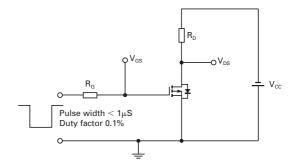




Basic gate charge waveform

Gate charge test circuit





Switching time waveforms

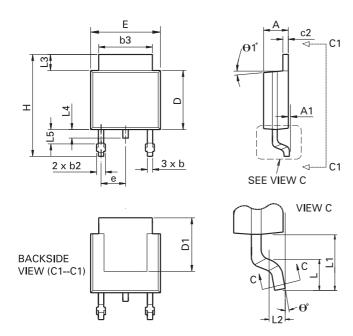
Switching time test circuit

ZXMP4A16K

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ZXMP4A16K

Package details - DPAK



Package dimensions

Dim.	Inches		Millimeters		Dim.	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	Н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
С	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	=	Ө1°	0°	10°	0°	10°
Е	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	_	-	-	-

Note: Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

Americas Asia Pacific Corporate Headquarters Zetex Inc Zetex (Asia Ltd) Zetex Semiconductors plc Zetex GmbH Streitfeldstraße 19 700 Veterans Memorial Highway 3701-04 Metroplaza Tower 1 Zetex Technology Park, Chadderton D-81673 München Hauppauge, NY 11788 Hing Fong Road, Kwai Fong Oldham, OL9 9LL Germany Hong Kong United Kingdom Telefon: (49) 89 45 49 49 0 Telephone: (1) 631 360 2222 Telephone: (852) 26100 611 Telephone: (44) 161 622 4444 Fax: (49) 89 45 49 49 49 Fax: (1) 631 360 8222 Fax: (852) 24250 494 Fax: (44) 161 622 4446 europe.sales@zetex.com usa.sales@zetex.com asia.sales@zetex.com hq@zetex.com

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